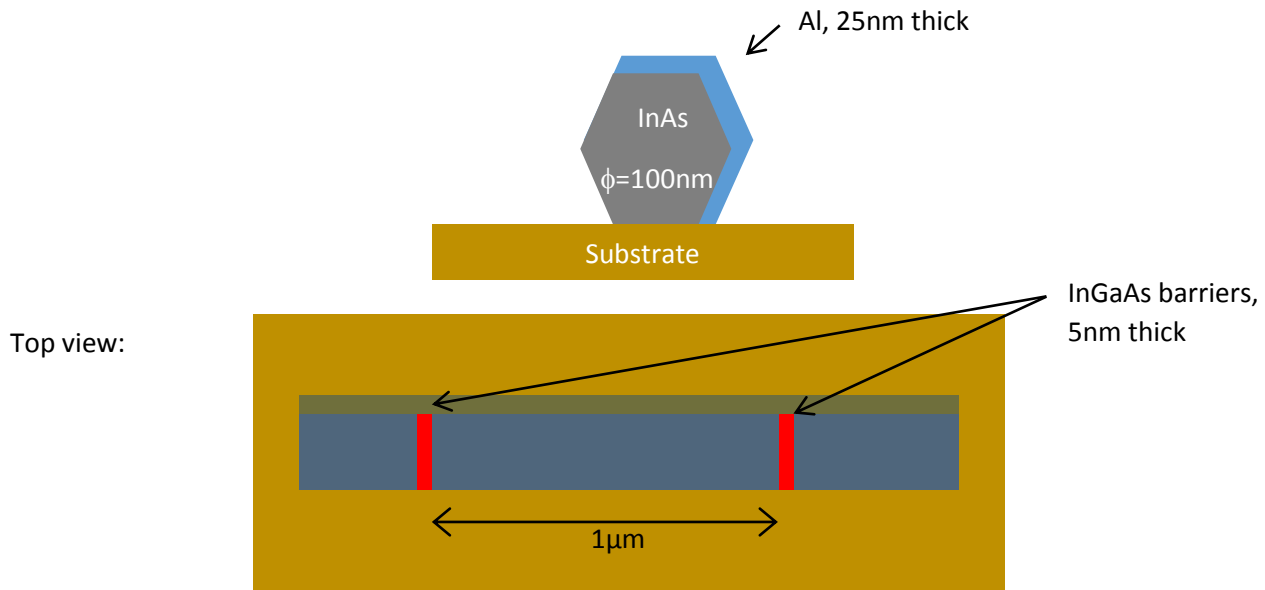
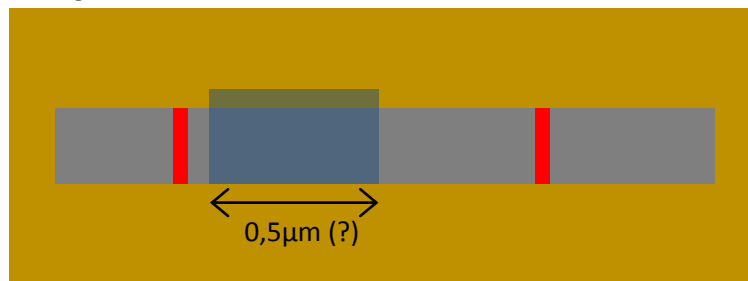


Fabrication process InAs/Al + InGaAs nanowires

- 1) Nanowire: hex nanowire, half covered, with 2 InGaAs barriers + backgate

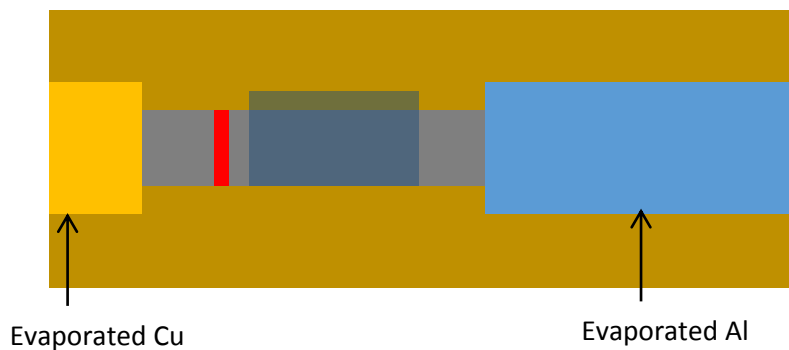


- 2) For a NIS junction:
a) Al etching



The idea is to cover the other barrier with the lead

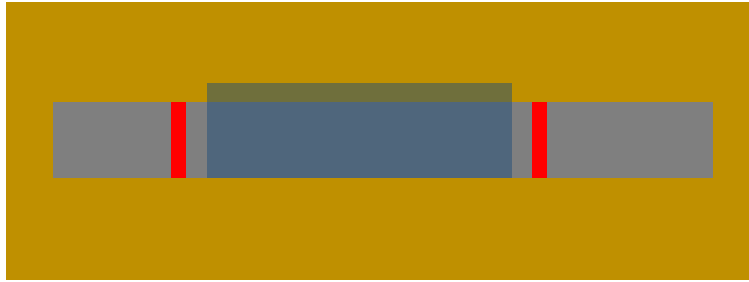
- b) Leads evaporation



3) For a NISIN device:

Same process, but with two barriers

a) Al etching



b) Evaporation of the copper leads + side gate

